



#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

- Low R<sub>DS(ON)</sub>:
  - $80 \text{ m}\Omega$  @V<sub>GS</sub> = -4.5V
  - 110 m $\Omega$  @V<sub>GS</sub> = -2.7V
  - 130 m $\Omega$  @V<sub>GS</sub> = -2.5V
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- "Green" Device (Note 4)

### **Mechanical Data**

- Case: SOT-26
- Case Material Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 2
- Ordering Information: See page 2
- Weight: 0.008 grams (approximate)

SOT-26





TOP VIEW

Internal Schematic

## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	-20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Drain Current (Note 1) Continuous	$T_A = 25$ °C $T_A = 70$ °C	I <sub>D</sub>	-3.4 -2.7	А
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	-12	A
Body-Diode Continuous Current (Note 1)		Is	2.0	А

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P <sub>D</sub>	1.25	W
Thermal Resistance, Junction to Ambient (Note 1); Steady-State	$R_{ hetaJA}$	100	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 1. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t ≤10s.
- 2. Repetitive Rating, pulse width limited by junction temperature.
- 3. No purposefully added lead.
- 4. Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

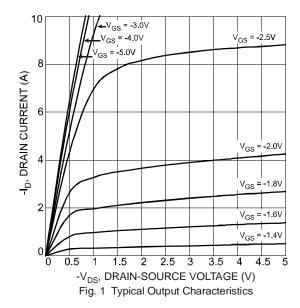


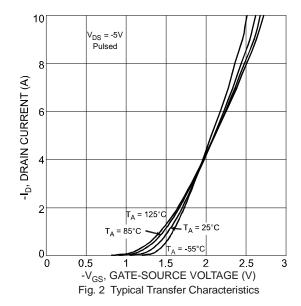
# **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	_	_	-1	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Body Leakage Current	I <sub>GSS</sub>	_	_	±100	nA	$V_{DS} = 0V, V_{GS} = \pm 12V$
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.6	_	-1.25	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
On State Drain Current (Note 5)	I <sub>D (ON)</sub>	-15	_	_	Α	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -5V
			51	80		$V_{GS} = -4.5V$ , $I_D = -4.5A$
Static Drain-Source On-Resistance (Note 5)	R <sub>DS (ON)</sub>	_	82	110	mΩ	$V_{GS} = -2.7V$ , $I_D = -3.8A$
	, ,		94	130		$V_{GS} = -2.5V, I_D = -3.7A$
Forward Transconductance (Note 5)	g <sub>FS</sub>	_	6.3	_	S	$V_{DS} = -10V$ , $I_D = -4.5A$
Diode Forward Voltage (Note 5)	$V_{SD}$	_	0.79	-1.26	V	$I_S = -1.7A$ , $V_{GS} = 0V$
Maximum Body-Diode Continuous Current (Note 1)		_	_	1.7	Α	_
DYNAMIC PARAMETERS (Note 6)						
Total Gate Charge	Qg	_	7.3	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_D = 4.5A$
Gate-Source Charge	Qgs	_	2.0	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_D = 4.5A$
Gate-Drain Charge	$Q_{gd}$	_	1.9	_	nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_D = 4.5A$
Turn-On Delay Time	t <sub>D(on)</sub>	_	12	_	ns	
Turn-On Rise Time		_	20	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time		_	38	_	ns	$R_L = 10\Omega$ , $R_G = 6\Omega$
Turn-Off Fall Time	t <sub>f</sub>	_	41	_	ns	
Input Capacitance	C <sub>iss</sub>	_	443	_	pF	404.44
Output Capacitance		_	125	_	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance		_	98	_	pF	] = 1.∪IVI⊓Z

Notes:

- 5. Test pulse width  $t=300\mu s$ . 6. Guaranteed by design. Not subject to production testing.







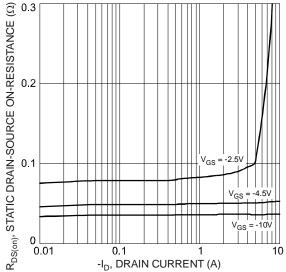


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

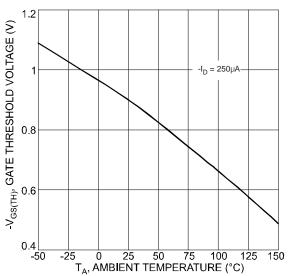


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

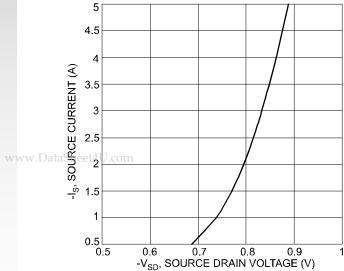
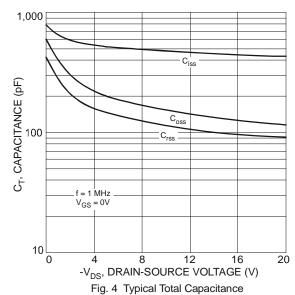


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage



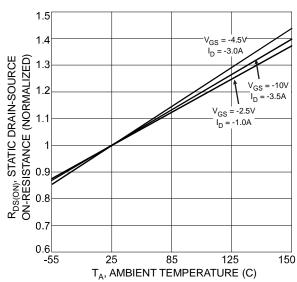


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

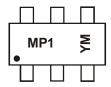


## Ordering Information (Note 7)

Part Number	Case	Packaging
DMP2130LDM-7	SOT-26	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**

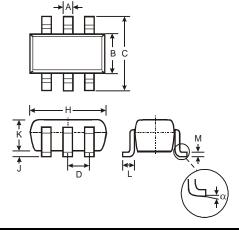


MP1 = Product Type Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key

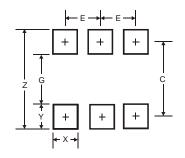
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Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

## **Package Outline Dimensions**



SOT-26					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D	_		0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
K	1.00	1.30	1.10		
L	0.35	0.55	0.40		
М	0.10	0.20	0.15		
α	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**



<b>Dimensions</b>	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C	2.40
ш	0.95

www.DataSheet4U.com

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